JJMICROELECTRONICS

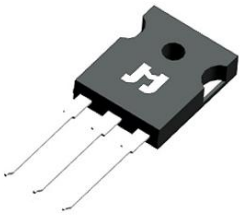
650V 75A Trench and Field Stop IGBT

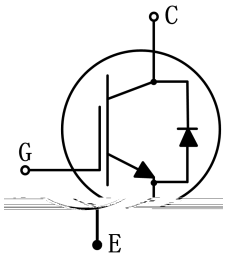
JJT75N65HEV

V_{CES}=650V

- I_C@75A@T_C=100
- $V_{CE(sat)}$=1.7V

TO-247





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V_{CES}	Collector-emitter voltage	650	V
V_{GES}	Gate-emitter voltage	±20	V
	Transient gate-emitter voltage(t_p 10μS, 0.010)	±30	V
I_C	Continuous collector current (T_C=25)	150	A
	Continuous collector current (T_C=100)	75	A
I_{CM}	Pulsed collector current, t_p limited by T_{vjmax}	300	A
I_F	Diode continuous forward current (T_C=100)	75	A
I_{FM}	Diode maximum current, t_p limited by T_{vjmax}	300	A
P_{tot}	Power dissipation (T_C=25)	652	W
	Power dissipation (T_C=100)	326	W
T_{vj}	Operating junction temperature range	-55 to +175	
T_{stg}	Storage temperature range	-55 to +175	

$R_{th(j-c)}$	Thermal resistance, junction to case for IGBT	-	0.23	K/ W
$R_{th(j-c)}$	Thermal resistance, junction to case for Diode	-	0.60	K/ W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	-	40	K/ W

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(T_{vj}=25 unless otherwise specified)

Static characteristics

BV_{CES}	Collector-emitter breakdown voltage	V_{GE}=0V, I_C=250μA	650	-	-	V
I_{CES}	Collector-emitter leakage current	V_{CE}=650V, V_{GE}=0V	-	-	50	μA
I_{GES}	Gate leakage current, forward	V_{GE}=20V, V_{CE}=0V	-	-	100	nA
	Gate leakage current, reverse	V_{GE}=-20V, V_{CE}=0V	-	-	-100	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{GE}=V_{CE}, I_C=1mA	4.7	5.1	5.5	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE}=15 V, I_C=75A	-	1.72	-	V
		V_{GE}=15V, I_C=75A, T_{vj} =175	-	2.3	-	V

Dynamic characteristics

C_{ies}	Input capacitance	V_{CE}=30V V_{GE}=0V f=1MHz	-	4241	-	pF
C_{oes}	Output capacitance		-	172	-	pF
C_{res}	Reverse transfer capacitance		-	21	-	pF
Q_g	Total gate charge	V_{CC}=520V V_{GE}=15V I_C=75A	-	130	-	nC

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Switching characteristics

$t_{d(on)}$	Turn-on delay time	V_{CC}=400V V_{GE}=0/15V I_C=75A R_G=10Ω Inductive load	-	53	-	ns
t_r	Rise time		-	132	-	ns
$t_{d(off)}$	Turn-off delay time		-	162	-	ns
t_f	Fall time		-	95	-	ns
E_{on}	Turn-on energy		-	3.3	-	mJ
E_{off}	Turn-off energy		-	2.1	-	mJ
E_{ts}	Total switching energy		-	5.4	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CC}=400V V_{GE}=0/15V I_C=75A R_G=10Ω Inductive load T_{vj} =175	-	53	-	ns
t_r	Rise time		-	128	-	ns
$t_{d(off)}$	Turn-off delay time		-	181	-	ns
t_f	Fall time		-	107	-	ns
E_{on}	Turn-on energy		-	4.8	-	mJ
E_{off}	Turn-off energy		-	2.6	-	mJ
E_{ts}	Total switching energy		-	7.4	-	mJ

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(T_{vj}=25 unless otherwise specified)

V_F	Diode forward voltage	I_F=75A	-	1.7	-	V
		I_F=75A,T_{vj}=175	-	1.4	-	V
t_{rr}	Diode reverse recovery time	V_R=400V I_F=75A di_F/dt=-450A/μs	-	129	-	ns
I_{rrm}	Diode peak reverse recovery current		-	14	-	A
Q_{rr}	Diode reverse recovery charge		-	778	-	nC
t_{rr}	Diode reverse recovery time	V_R=400V I_F=75A di_F/dt=-450A/μs T_{vj}=175	-	172	-	ns
I_{rrm}	Diode peak reverse recovery current		-	22	-	A
Q_{rr}	Diode reverse recovery charge		-	2200	-	nC

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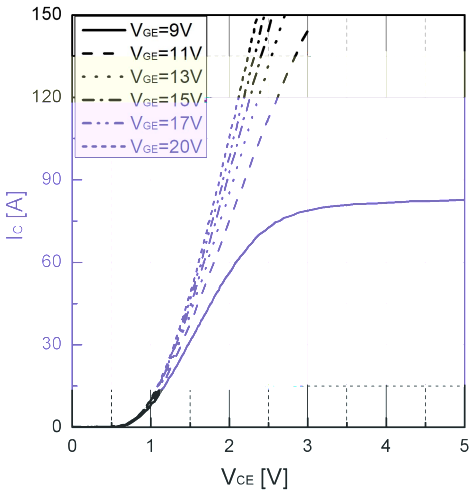


Fig 1. Typical output characteristic (T_{vj}=25)

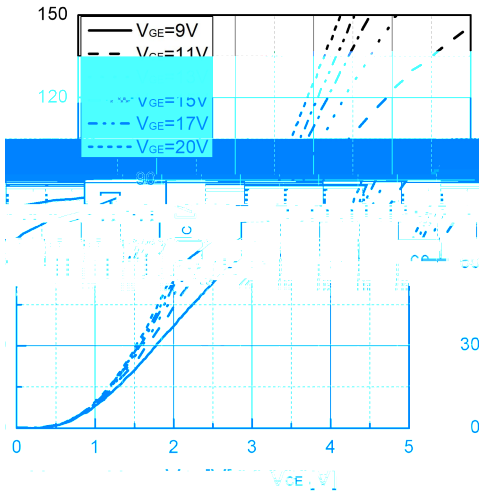


Fig 2. Typical output characteristic(T_{vj}=175)

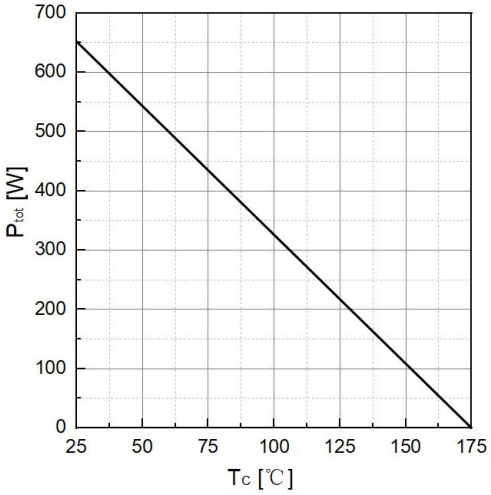


Fig 3. Power dissipation as a function of T_C

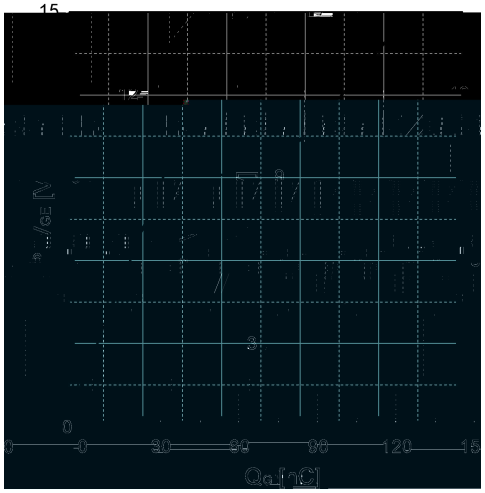


Fig 4. Typical Gate charge

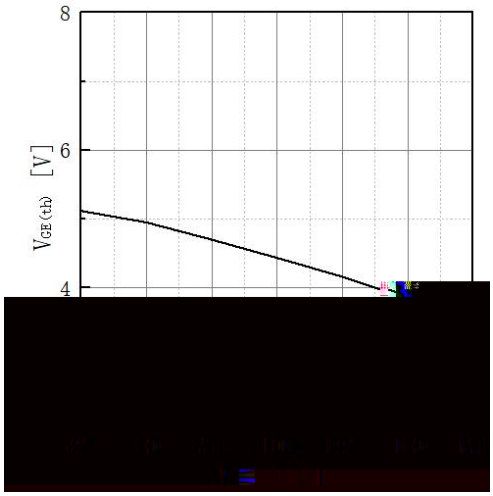


Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj} (I_C=1mA)

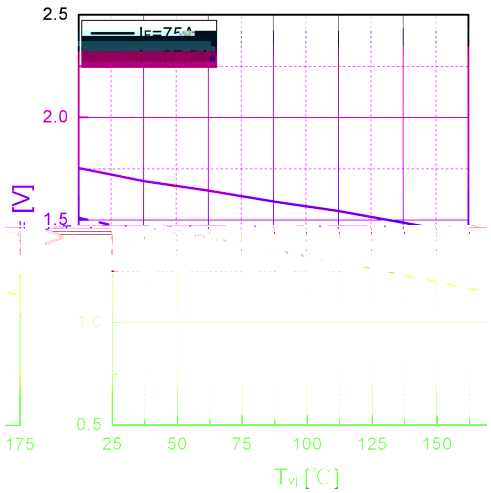


Fig 6. Typical V_F as a function of T_{vj}

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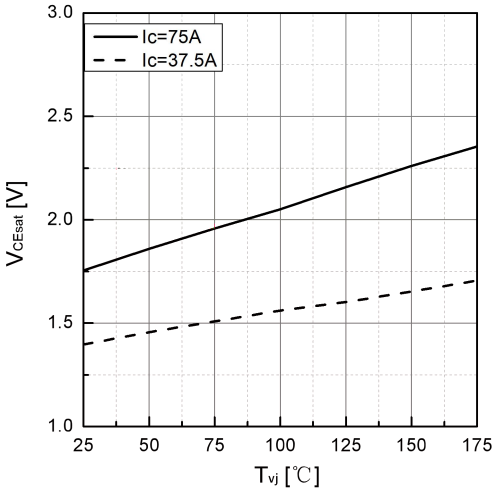


Fig 7. Typical V_{CEsat} as a function of T_{vj}

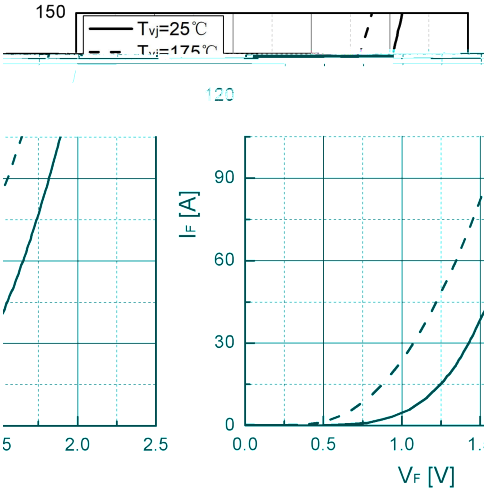


Fig 8. Typical I_F as a function of V_F

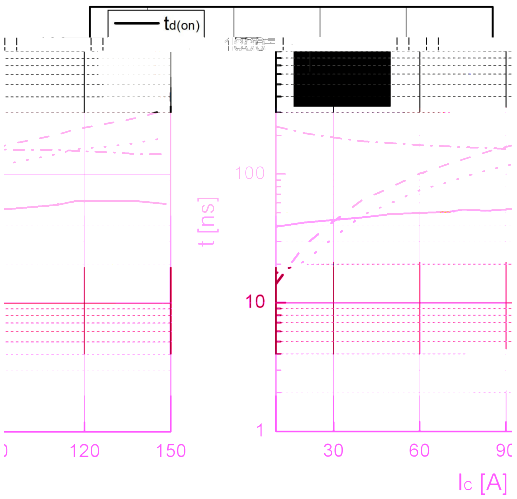


Fig 9. Typical switching time as a function of I_C

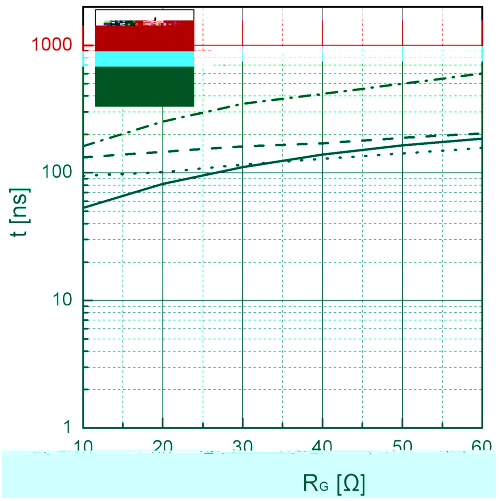


Fig 10. Typical switching times as a function of R_G

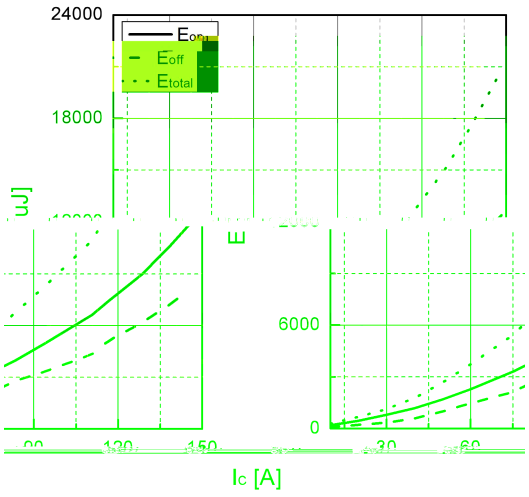


Fig 11. Typical switching energy losses as a function of I_C

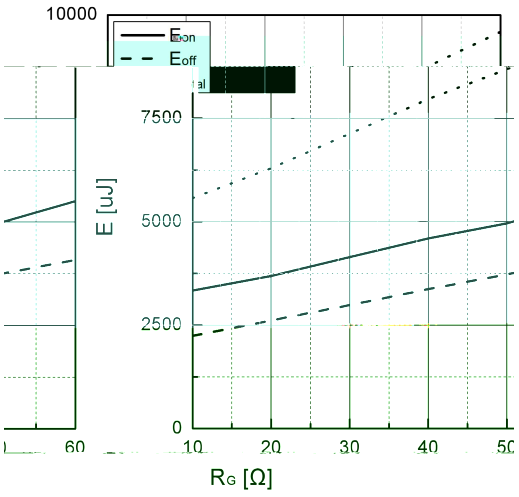


Fig 12. Typical switching energy losses as a function of R_G

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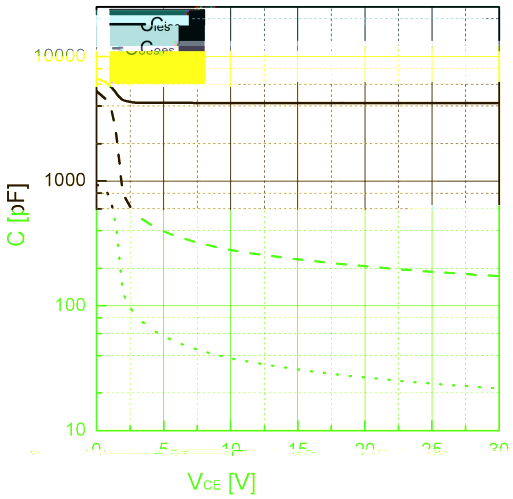


Fig 13. Typical capacitance as a function of V_{CE} (f=1Mhz, V_{GE}=0V)

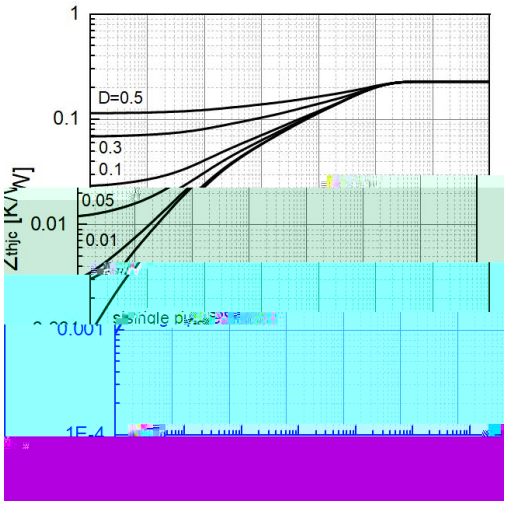


Fig 14. Transient thermal impedance of IGBT

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Dimensions				
		Inches		
	Max.	Min.	Typ.	Max.
	16.10	0.610	0.622	0.634
	21.20	0.819	0.827	0.835
	.30	0.776	0.787	0.799
		0.071	0.079	0.087
		0.075	0.083	0.091
		0.039	0.047	0.055
		0.207	-	0.222
		0.189	0.197	0.205
		0.075	0.079	0.083
		087	0.093	0.098
			0.024	0.031
			0.118	0.126
			0.122	0.130

Date

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